$$\Gamma(r) = \sum \Gamma(K_n) e^{iK_n \cdot r}$$

倒格矢:
$$b_1 = \frac{2\pi[a_2 \times a_3]}{\Omega}$$
 $b_2 = \frac{2\pi[a_1 \times a_3]}{\Omega}$ $b_3 = \frac{2\pi[a_1 \times a_2]}{\Omega}$

单电子近似电子的势函数是只关于r的函数

德布罗意: $P = \frac{h}{\lambda}$

量子牛顿方程: $f = \hbar \frac{dk}{dt} = \frac{dp}{dt}$

有效质量:
$$rac{1}{\hbar^2} \Biggl(rac{\mathbf{d}^2 E}{\mathbf{d} k^2}\Biggr)_{k=0} = rac{1}{m_{\mathrm{n}}^*}$$

电子速度: $v = \frac{\hbar k}{m_{v*}}$

E 到E+dE 之间被电子占据的量子态f(E)g(E)dE

导带有效能态密度: $N_c=2(rac{m_n^*k_0T}{2\pi\hbar^2})^{rac{3}{2}}$

$$p=N_{
u}exp(rac{E_{v}-E_{F}}{k_{0}T}) \quad n=N_{c}exp(-rac{E_{c}-E_{F}}{k_{0}T})$$

质量作用定律:
$$np=N_cN_
u\exp(-rac{E_c-E_
u}{k_0T})=N_cN_
u\exp(-rac{E_g}{k_0T})=n_i^2$$

本征半导体:
$$E_i=E_F=rac{E_c+E_
u}{2}+rac{k_0T}{2}\lnrac{N_
u}{N_c}=rac{E_c+E_
u}{2}+rac{3k_0T}{4}\lnrac{m_p^*}{m_n^*}$$

可借助质量作用定律推得:

$$n = n_i \exp(rac{E_F - E_i}{k_0 T})$$
 $p = n_i \exp(rac{E_i - E_F}{k_0 T})$

电中性方程:
$$ho = q(N_D + p - n - N_A - n_D + p_A)$$

杂志饱和电离:
$$E_F=E_c+k_0T\ln(rac{N_D}{N_C})$$
 $E_F=E_{
m i}+k_0T\ln(rac{N_D}{n_i})$

简并半导体判断条件:

$$\left\{egin{aligned} E_c-E_F > 3k_0T, 非简并\ 0 < E_c-E_F < 3k_0T,$$
 弱简并 $E_c-E_F < 0$,简并

简并半导体: $N_D=0.68N_c[1+2\exp(rac{\triangle E_D}{k_0T})]$

电离杂质散射: $P_i \propto N_i T^{-\frac{3}{2}}$

长纵声学波: $P_s \propto T^{\frac{3}{2}}$

均匀导体的电流密度: $J=rac{I}{s}=rac{V}{Rs}=rac{l|E|}{Rs}=\sigma |E|$

平均迁移率: $\mu = \frac{q\tau}{m^*}$

 $\sigma = nq\mu_{\rm n} + pq\mu_{\rm p}$

迁移率: $\mu = \frac{q}{m^*} \frac{1}{AT^{\frac{3}{2}} + BN_i T^{-\frac{3}{2}}}$

对于n型半导体温度不太高时 $R_H \approx -\frac{1}{nq}$

霍尔效应:对于p型半导体温度不太高时 $R_H \approx -\frac{1}{pq}$

本征情况
$$R_H pprox rac{1-b^2}{n_i g(1+b)^2}$$

直接复合: $au = \frac{\Delta p}{U_d} = \frac{1}{r[(n_0+p_0)+\Delta p]}$

俘获和发射电子能力联系:
$$s_n=r_nn_1$$
 $n_1=N_c\exp(-\frac{E_c-E_t}{k_0T})$ 通过复合中心复合: $U=\frac{N_tr_nr_p(np-n_i^2)}{r_n(n+n_1)+r_p(p+p_1)}=\frac{(np-n_i^2)}{\tau_p(n+n_1)+\tau_n(p+p_1)}$ $\tau=\frac{\Delta p}{U}=\frac{r_n(n_0+n_1+\Delta p)+r_p(p_0+p_1+\Delta p)}{N_tr_nr_p(n_0+p_0+\Delta p)}$ ps: $n_t=$ 可以通过 $\frac{N_t(r_nn+r_pp_1)}{r_n(n+n_1)+r_p(p+p_1)}$ 推得另外书上和ppt中的公式是错的

肖克利-瑞德公式: $au = rac{\Delta p}{U} = au_p rac{n_0 + n_1}{n_0 + p_0} + au_n rac{p_0 + p_1}{n_0 + p_0} \quad au = au_p = rac{1}{N_t r_p} \quad au = au_n = rac{1}{N_t r_n}$

一维扩散方程: $rac{\partial \Delta p(x)}{\partial t} = D_p rac{d^2 \Delta p(x)}{dx^2} - rac{\Delta p(x)}{ au}$

一维稳态扩散方程: $-\frac{dS_p(x)}{dx} = D_p \frac{d^2 \Delta p(x)}{dx^2} = \frac{\Delta p(x)}{\tau_p}$

表明非平衡载流子浓度从光照表面向内部按指数衰减: $\Delta p(x) = (\Delta p)_0 e^{-x/L_p}$

爱因斯坦关系式: $\frac{D}{\mu} = \frac{kT}{q}$

连续性方程: $\frac{\partial p}{\partial t} = D_p \frac{\partial^2 p}{\partial x^2} - \mu_p |E| \frac{\partial p}{\partial x} - \mu_p p \frac{\partial |E|}{\partial x} + g_p - \frac{\Delta p}{\tau_p}$

线性缓变结: $N_D - N_A = \alpha_j(x - x_j)$

突变结接触电势差: $qV_D=E_{Fn}-E_{Fp}$ $V_D=rac{kT}{q}\ln(rac{N_AN_D}{n^2})$

$$\mathbf{P}^{+}\mathbf{N}\left(N_{A}\gg\ N_{D}
ight) \quad X_{D}=\sqrt{rac{2arepsilon_{r}arepsilon_{0}V_{D}}{qN_{D}}}\longrightarrow X_{D}pprox x_{n} \qquad \mathbf{N}^{+}\mathbf{P}$$
结 $\left(N_{D}\gg N_{A}
ight) \quad X_{D}=\sqrt{rac{2arepsilon_{r}arepsilon_{0}V_{D}}{qN_{A}}}\longrightarrow X_{D}pprox x_{D}$

正偏压P-N结: $\Delta n(x) = \dot{\Delta n(-x_p)} \exp\left(rac{x+x_p}{L_n}
ight)$ $\Delta p(x) = \Delta p(x_n) \exp\left(-rac{x-x_n}{L_p}
ight)$

反偏压P-N结: $\Delta n(x) = -n_{p0} \exp\left(rac{x+x_p}{L_n}
ight)$ $\Delta p\left(x
ight) = -p_{n0} \exp\left(-rac{x-x_n}{L_p}
ight)$

理想P-N结I-V特性: $J=J_s\left[\exp\left(rac{qV}{kT}
ight)-1
ight]$ $J_s=\left(rac{qD_pn_i^2}{L_pN_D}+rac{qD_nn_i^2}{L_nN_A}
ight)$

理想P-N结I-V特性修正:

正向偏压: $rac{J_{fd}}{J_r} \propto rac{2n_i L_p}{N_D X_D} {
m exp}(qV/2kT)$

反向偏压:

$$J_G = qGX_D = qrac{n_i}{2 au}X_D$$

$$rac{J_{rd}}{J_G}=2rac{n_i}{N_D}rac{L_p}{X_D}$$

平行板电容: $C_T = \frac{A\varepsilon_0\varepsilon_r}{X_D}$

平行权电合、
$$C_T = \frac{1}{X_D}$$

$$p_{(x)} = n_i e^{\frac{E_i(x) - E_F}{kT}} = p_{P0} e^{\frac{E_F - E_i(x_p)}{kT}} e^{\frac{E_i(x) - E_F}{kT}} = p_{P0} e^{\frac{-qV(x)}{kT}} = p_{N0} e^{\frac{qV_D - qV(x)}{kT}}$$

$$n_{(x)} = n_i e^{\frac{E_F - E_i(x)}{kT}} = n_{N0} e^{\frac{E_i(x_n) - E_F}{kT}} e^{\frac{E_F - E_i(x)}{kT}} = n_{N0} e^{\frac{qV(x) - qV_D}{kT}} = n_{P0} e^{\frac{qV(x)}{kT}}$$

泊松方程: $\frac{d^2V}{dx^2} = -\frac{\rho(x)}{\varepsilon_r \varepsilon_0}$

肖特基二极管空间电荷区宽:
$$d=\left[rac{2arepsilon_0arepsilon_r}{qN_D}(\phi_{ns}-\phi_n)
ight]^{1/2}=\left(rac{2arepsilon_0arepsilon_r}{qN_D}V_D
ight)^{1/2}$$

适用于势垒宽度>>电子平均自由程:

$$J=J_{\scriptscriptstyle SD}[\exp(qV/kT)-1]$$
 $J_{\scriptscriptstyle SD}=rac{q^2D_nn_0}{kT}[rac{2qN_D}{arepsilon_{\scriptscriptstyle E}}(V_D-V)]^{rac{1}{2}}\exp(rac{-qV_D}{kT})$

表面空间电荷层的电场:

$$E^2(x) = \left(rac{2kT}{q}
ight)^2 \left(rac{q^2p_{p0}}{2arepsilon_s kT}
ight) \left\{ \left[\exp\left(-rac{qV}{kT}
ight) + rac{qV}{kT} - 1
ight] + rac{n}{p_{p0}} \left[\exp\left(rac{qV}{kT}
ight) - rac{qV}{kT} - 1
ight]
ight\} \ E(x) = \pm rac{2kT}{qL_D} F\left(rac{qV(x)}{kT}, rac{n_{p0}}{p_{p0}}
ight) \quad L_D = \left(rac{arepsilon_S kT}{q^2p_0}
ight)^{1/2}$$

耗尽层宽度最大值: $d_{\max} = \left(\frac{2\epsilon_s}{q} \frac{2V_B}{N_A}\right)^{1/2}$ 外加电场被反型层屏蔽,耗尽层宽度达到最大

$$\left|C_s = \left|rac{dQ_s}{dV_s}
ight| = rac{arepsilon_s}{L_D} \left\{ \left[-\exp\left(-rac{qV_s}{kT}
ight) + 1
ight] + rac{n_{p0}}{p_{p0}} \left[\exp\left(rac{qV_s}{kT}
ight) - 1
ight]
ight\} / F\left(rac{qV_s}{kT}, rac{n_{p0}}{p_{p0}}
ight)$$

绝缘层单位面积电容: $C_{ox}=rac{\mathcal{E}_{ox}}{d_{ox}}$

平带电容:

$$C_{FBS} = \lim_{V_s o 0} rac{dQ_s}{dV_s} = rac{\sqrt{2}arepsilon_s}{L_D} \left(1 + rac{n_{p0}}{p_{p0}}
ight)^{1/2} pprox rac{\sqrt{2}arepsilon_s}{L_D} \quad C_{FB} = C_{_{FB}} = C_{_{ox}}/1 + rac{arepsilon_{ox}}{d_{ox}} \left(rac{kT}{q^2N_A arepsilon_s}
ight)^{rac{1}{2}}$$

高频情况反型层电子产生复合更不上高频信号的变化: $\frac{C'_{\min}}{C_{\text{ox}}} = \frac{1}{1+\frac{4\epsilon_s kT}{a} \ln\left(\frac{N_A}{a}\right)]^{1/2}}$

阈值电压: $V_T = \phi_{ms} - rac{Q_{ox}}{C_{ox}} - rac{Q_B}{C_{ox}} + 2\phi_F$

反型层电荷: $Q_n(y) = -C_{oX}[V_{GS} - V(y) - V_T]$ 萨支唐方程: $I_{DS} = \beta \left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2 \right] \quad \beta \equiv \frac{\mu_n W C_{ox}}{L}$ 沟道夹断: $I_{DSat} = \frac{\beta}{2}(V_{GS} - V_T)^2 \quad V_{DSat} \equiv V_{GS} - V_T$